Zener Diode Array

STZ5.6N

●Applications

Constant voltage control
For the ESD measure of a signal line

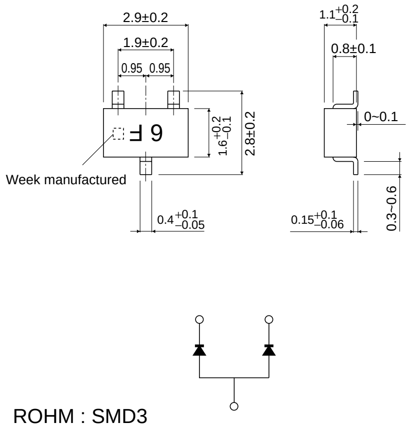
●Features

1) Designed for mounting on small surface areas
2) High reliability
3) Composite type with two anode/cathode elements

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



ROHM : SMD3
EIAJ : SC-59

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Power dissipation	P*	200	mW
Junction temperature	Tj	150	˚C
Storage temperature	Tstg	−55~+150	˚C

∗ Total of 2 elements

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Zener voltage	V_Z	5.31	−	5.92	V	I_Z=5mA
Reverse current	I_R	−	−	1.00	µA	V_R=2.5V
Operating resistance	Z_Z	−	−	60	Ω	I_Z=5mA
Rising operating resistance	Z_{ZK}	−	−	200	Ω	I_Z=0.5mA
Capacitance between terminals	C_T	−	12	−	pF	f=1MHz, V_R=5V

●Others

Item	Standard1	IEC1000-4-2
Device configuration	Charge/discharge capacitance : 200pF±10% Discharge resistance : 400Ω ±10%	Charge/discharge capacitance : 150pF Discharge resistance : 330Ω
Judgment contents	5 repetitions No spark or smoke emitted : ±25kV No element destruction : ±20kV No malfunction : ± 8kV	10 repetitions No malfunction Contact : ± 8kV Suspended : ±15kV

●Electrical characteristic curves (Ta=25°C)

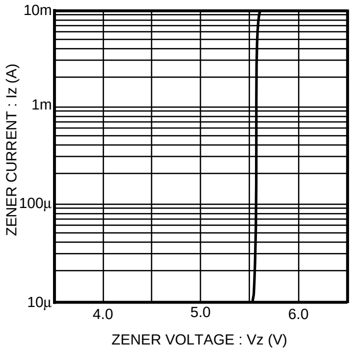


Fig.1 Zener characteristics

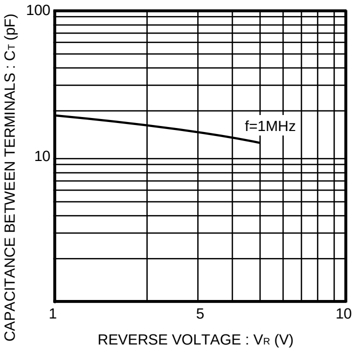


Fig.2 Capacitance between terminals characteristic

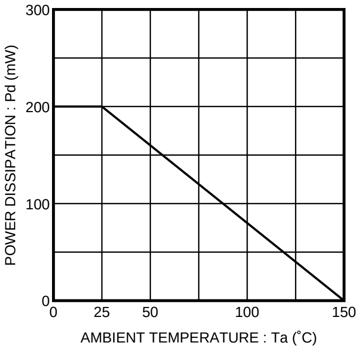


Fig.3 Derating curve